## SYNCHROTRON BASED INFRARED TECHNIQUE TO STUDY OXIDE FILMS ON METALS

Vivek Srinivasamurthi<sup>1</sup>, Hugh S.Isaacs<sup>2</sup>, Lisa Miller<sup>3</sup>, Nebojsa Marinkovic<sup>4</sup>, Gordana Adzic<sup>2</sup> and Sanjeev Mukerjee<sup>1</sup>

<sup>1</sup>Department of Chemistry, Northeastern University, Boston, MA-02115

<sup>2</sup> Materials Science Department

And <sup>3</sup> National Synchrotron Light Source Brookhaven National Laboratory, Upton, NY-11973

<sup>4</sup> Center for Synchrotron Biosciences, Albert Einstein College of Medicine, NY- 10461

The advantages of synchrotrons as a unique source of infrared radiation, in the mid and far spectral region have been clearly demonstrated [1,2]. In this presentation, we describe techniques involved in studying surface species using infrared microscopy.

Tantalum oxide films have been the subject of study in many areas [3-5] including corrosion, integrated circuits and capacitors. Infrared reflectance spectroscopy measurements include the use of multiple external reflections on anodic oxides films of Ta grown in acid solutions [6]. In our work, we employed synchrotron based infrared micro-spectroscopy to monitor and characterize anodic oxide films grown on valve metals (e.g., Al, Ta, and Zr) in near-neutral solutions. Fig.1 and Fig. 2 show the infrared reflectance measurements on anodic oxide films grown on Al and Ta respectively in neutral borate solutions (pH 8.4) at a current density of 10mA/cm<sup>2</sup> until the desired voltage was reached. Aluminum oxide has a strong Al-O bond vibration at 950 cm<sup>-1</sup> while the vibration of the Ta-O bond exhibits a broad peak at 925 cm<sup>-1</sup>. Shifts in the Ta-O vibration at higher potentials have been observed. The shifts could be due to a change in the structure of the oxide film. The characteristics of the oxide films on these valve metals including the type of oxides and the metal-to-oxygen bond vibrations will be discussed in relation to their growth kinetics, thickness and solution composition.

## Acknowledgment

This work was performed under the auspices of the U.S. Department of Energy, Division of Materials Science, Office of Basic Energy Sciences under Contract No. DE-AC02-76CH00016

## References

- Duncan W.D. and Williams G.P., *Appl. Optics*, 22, 2914 (1998).
- Carr, G.L., Dumas, P., Hirschmugl, C.J. and Williams, G.P., Infrared synchrotron radiation programs at the National Synchrotron Light Source. Nuovo Cimento della Societa Italiana di Fisica, [Sezione] D: Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics; 20D (4), 375-395 Apr 1998. ISSN: 0392-6737.
- 3. L.Young, *Anodic Oxide films*, Academic press, London (1961)
- 4. Young L., J. Electrochem. Soc., 124, 528 (1977).

- Li Y.M. and Young L., *J.Electrochem. Soc.*, 148, B337 (2001).
- 6. Takamura T. and Kihara-Morishita H., *J. Electrochem. Soc.*, **122**, 386 (1975).

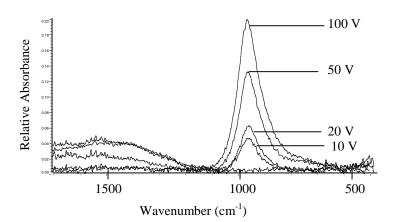
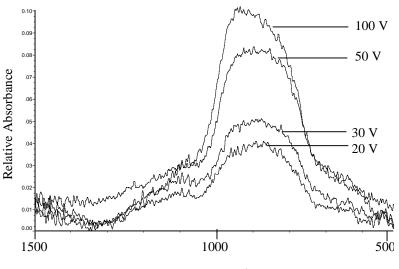


Fig 1. Grazing angle IR spectra of Aluminum oxide grown to different thickness



Wavenumber (cm<sup>-1</sup>)

Fig 2. Grazing angle IR spectra of Tantalum oxide grown to different thickness